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PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Hitoshi Shimizu, et al  
App. No. : 09/918,018  
Filed : July 30, 2001  
For : SEMICONDUCTOR LASER DEVICE  
HAVING LOWER THRESHOLD CURRENT  
Examiner : Unknown  
Group Art Unit : 2881

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*Mark J. Gallagher*  
Mark J. Gallagher, Reg. No. 43,622

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

Enclosed is form PTO-1449 listing six (6) references that are also enclosed. This Information Disclosure Statement is being filed before the mailing date of a final action under 37 C.F.R. § 1.113 and before the mailing date of a Notice of Allowance under § 1.311. A certification under 37 C.F.R. § 1.97(e) is set forth below. Thus, no fee is required as set forth below in 37 C.F.R. § 1.97(c).

CERTIFICATION UNDER 37 C.F.R. § 1.97(e)(1)

I hereby certify that each item of information contained in this Statement was first cited in a communication from a foreign Patent Office in a counterpart foreign application not more than three months prior to the filing of this Information Disclosure Statement.

Respectfully submitted,  
KNOBBE, MARTENS, OLSON & BEAR, LLP

Dated: 7/16/03

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FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.  
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09/918,018INFORMATION DISCLOSURE STATEMENT  
BY APPLICANT

(USE SEVERAL SHEETS IF NECESSARY)

APPLICANT  
Hitoshi Shimizu *et al*FILING DATE  
July 30, 2001GROUP  
2881

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)

## FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
	WO 00/38287	29.06.00	PCT				
	WO 01/33677 A2	10.05.01	WIPO				

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
	H. Shimizu et al., 1.2 um range GaInAs S QW lasers using Sb as surfactant, <u>ELECTRONICS LETTERS</u> , Vol. 36, No. 16, August 3, 2000, 2 pages.
	X. Yang et al., Molecular beam epitaxial growth of InGaAsN:Sb/GaAs quantum wells for long-wavelength semiconductor lasers, <u>Applied Physics Letters</u> , Vol. 75, No. 2, July 12, 1999, pp. 178-180.
	X. Yang et al., Photoluminescence of as-grown and thermally annealed InGaAsN/GaAs quantum wells grown by molecular beam epitaxy, <u>J. Vac. Sci. Technol.</u> , Vol. B, No. 17(3), May/June 1999, pp. 1144-1146.
	X. Yang et al., Low-Threshold 1.3-um InGaAsN:Sb-GaAs Single-Quantum-Well Lasers Grown by Molecular Beam Epitaxy, <u>IEEE PHOTONICS TECHNOLOGY LETTERS</u> , Vol. 12, No. 2, February 2000, pp. 128-130.

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EXAMINER	DATE CONSIDERED
<p>*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.</p>	